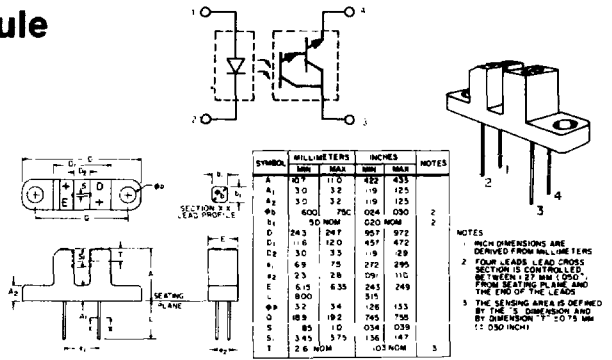


CNY29 Optointerrupter GaAs Infrared Emitting Diode and NPN Silicon Photo-Darlington Amplifier Module

The CNY29 is a gallium arsenide, infrared emitting diode coupled with a silicon photo-Darlington in a plastic housing. The gap in the housing provides a means of interrupting the signal with tape, cards, shaft encoders, or other opaque material, switching the output transistor from an "ON" into an "OFF" state.

FEATURES:

- Low cost, plastic module
- Non-contact switching
- Solid-state reliability
- I/O compatible with integrated circuits



absolute maximum ratings: (25°C) (unless otherwise specified)

Storage and Operating Temperature -55° to 85°C. Lead Soldering Time (at 260°C) 10 seconds.

INFRARED EMITTING DIODE			
Power Dissipation	*100	milliwatts	
Forward Current (Continuous)	60	milliamps	
Forward Current (peak, 100 μs, 1% duty cycle)	1	amp	
Reverse Voltage	3	volts	
*Derate 1.67 mW/°C above 25°C ambient			

PHOTO-DARLINGTON			
Power Dissipation	**150	milliwatts	
Collector Current (Continuous)	100	milliamps	
V _{CEO}	25	volts	
V _{ECO}	7	volts	
**Derate 2.5mW/°C above 25°C ambient			

individual electrical characteristics (25°C)

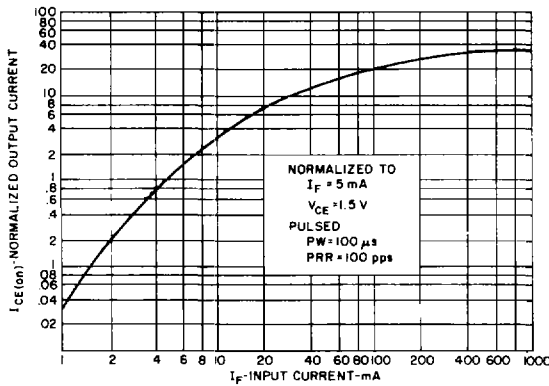
INFRARED EMITTING DIODE	TYP.	MAX.	UNITS
Forward Voltage V _F (I _F = 10 mA)	1.2	1.7	volts
Reverse Current I _R (V _R = 2V)	—	10	μamps
Capacitance C _J (V = 0, f = 1 MHz)	150	—	pf

PHOTO-DARLINGTON	MIN.	MAX.	UNITS
Breakdown Voltage V _{(BR)CEO} (I _C = 10 mA)	25	—	volts
Breakdown Voltage V _{(BR)ECO} (I _E = 100μa)	7	—	volts
Collector Dark Current I _{CEO} (V _{CE} = 10V, I _F = 0, H = 0)	—	100	nA

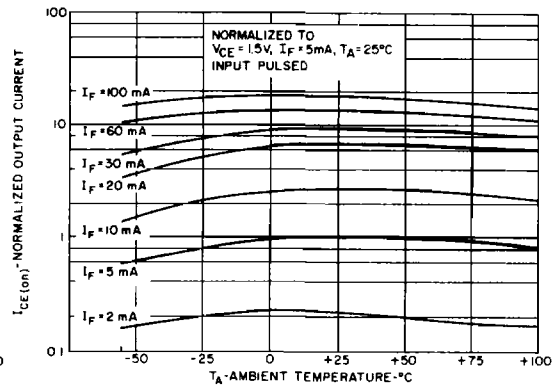
coupled electrical characteristics (25°C)

	MIN.	TYP.	MAX.	UNITS
Output Current (I _F = 20mA, V _{CE} = 5V)	2500	—	—	μamps
Saturation Voltage (I _F = 20mA, I _C = 0.5 mA)	—	—	1.2	volts
Switching Speeds (V _{CE} = 10V, I _C = 2 mA, R _L = 100Ω)				
On Time (t _d + t _r)	—	150	—	μsecs
Off Time (t _s + t _f)	—	150	—	μsecs

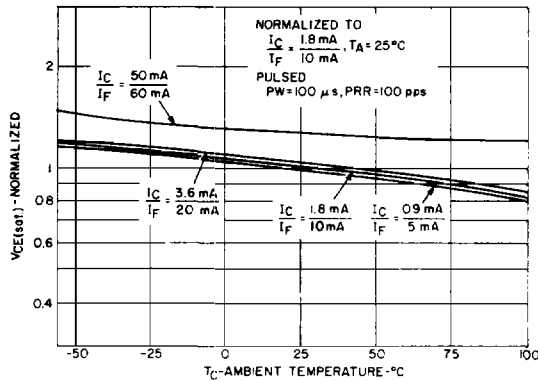
TYPICAL CHARACTERISTICS



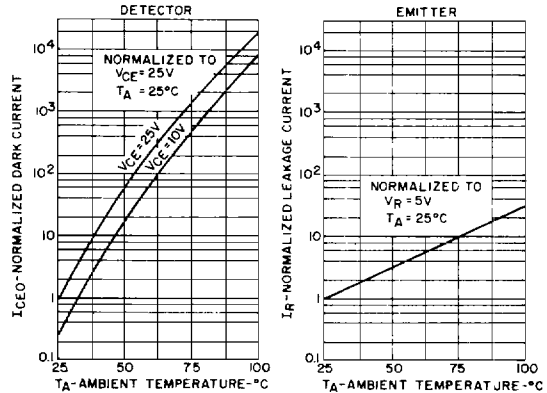
1. OUTPUT CURRENT VS. INPUT CURRENT



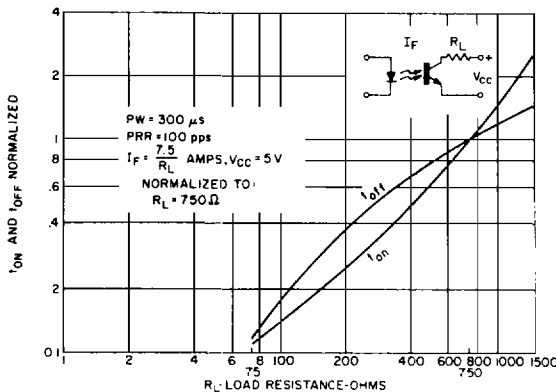
2. OUTPUT CURRENT VS. TEMPERATURE



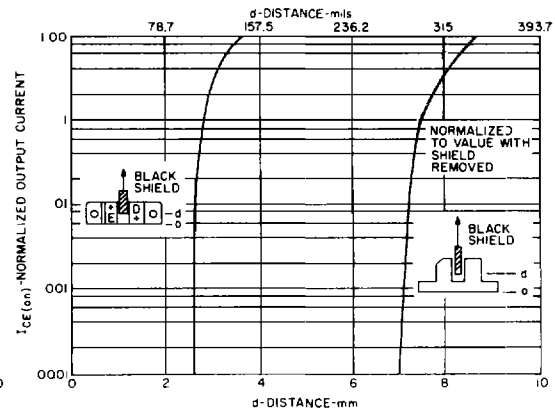
3. $V_{CE(sat)}$ VS. TEMPERATURE



4. LEAKAGE CURRENTS VS. TEMPERATURE



5. SWITCHING SPEED VS. R_L



6. OUTPUT CURRENT VS. SHIELD DISTANCE